

74AHC245; 74AHCT245

Octal bus transceiver; 3-state

Rev. 05 — 28 April 2009

Product data sheet

1. General description

The 74AHC245; 74AHCT245 is a high-speed Si-gate CMOS device.

The 74AHC245; 74AHCT245 is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions.

The 74AHC245; 74AHCT245 features an output enable input (\overline{OE}), for easy cascading, and a send and receive direction control input (DIR).

\overline{OE} controls the outputs so that the buses are effectively isolated.

2. Features

- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - ◆ For 74AHC245: CMOS level
 - ◆ For 74AHCT245: TTL level
- ESD protection:
 - ◆ HBM EIA/JESD22-A114E exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V
 - ◆ CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC245D 74AHCT245D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHC245PW 74AHCT245PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHC245BQ 74AHCT245BQ	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85$ mm	SOT764-1



4. Functional diagram

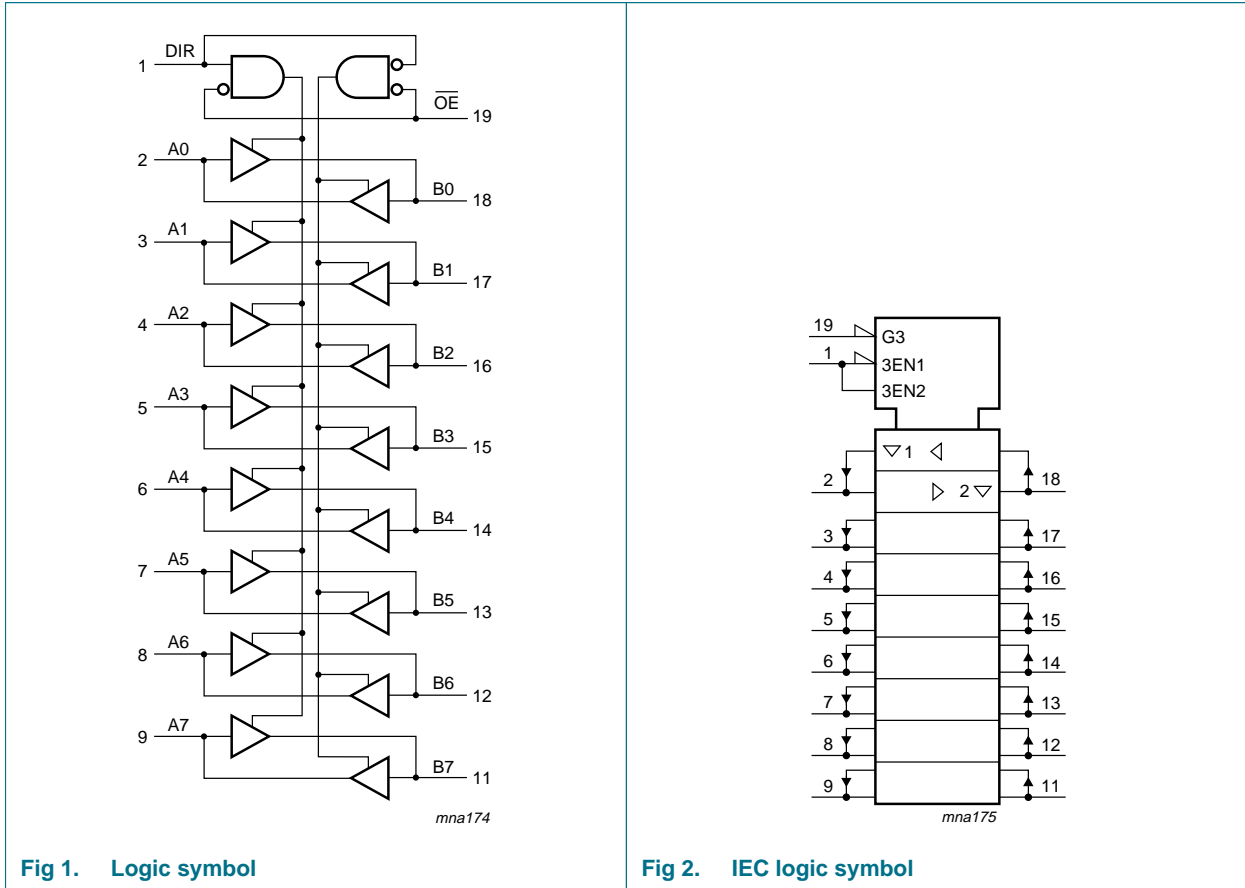
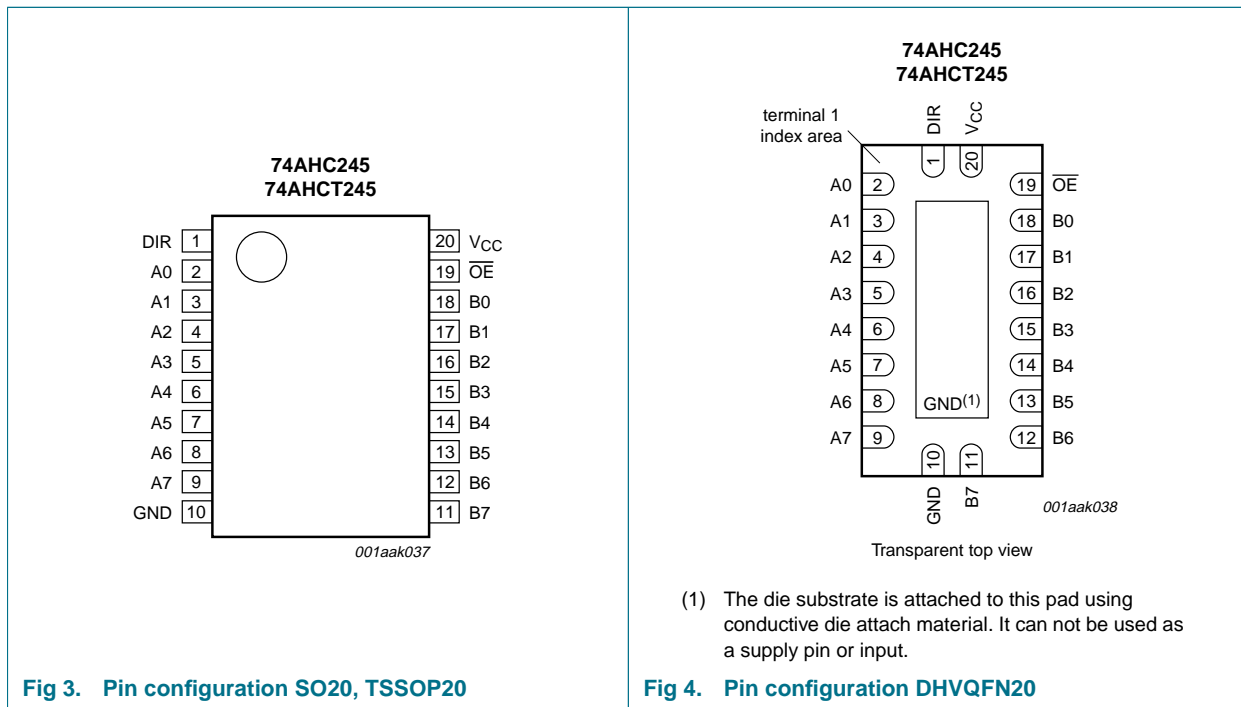


Fig 1. Logic symbol

Fig 2. IEC logic symbol

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DIR	1	direction control input
A0	2	data input/output
A1	3	data input/output
A2	4	data input/output
A3	5	data input/output
A4	6	data input/output
A5	7	data input/output
A6	8	data input/output
A7	9	data input/output
GND	10	ground (0 V)
B7	11	data input/output
B6	12	data input/output
B5	13	data input/output
B4	14	data input/output
B3	15	data input/output
B2	16	data input/output

Table 2. Pin description ...continued

Symbol	Pin	Description
B1	17	data input/output
B0	18	data input/output
\overline{OE}	19	output enable input (active LOW)
V_{CC}	20	supply voltage

6. Functional description

Table 3. Function table^[1]

Control		Input/output		
\overline{OE}	DIR	An	Bn	
L	L	A = B	inputs	
L	H	inputs	B = A	
H	X	Z	Z	

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	^[1] -20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	^[1] -20	+20	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)	-25	+25	mA
I_{CC}	supply current		-	+75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[2] -	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] For SO20 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
 For TSSOP20 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.
 For DHVQFN20 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74AHC245						
V _{CC}	supply voltage		2.0	5.0	5.5	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 3.0 V to 3.6 V	-	-	100	ns/V
		V _{CC} = 4.5 V to 5.5 V	-	-	20	ns/V
74AHCT245						
V _{CC}	supply voltage		4.5	5.0	5.5	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 4.5 V to 5.5 V	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC245										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -50 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -50 μA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = -50 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
I _O = -8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.80	-	3.70	-	V		
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V		

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.25	-	±2.5	-	±10.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	4.0	-	40	-	80	μA
C _I	input capacitance	V _I = V _{CC} or GND	-	3	10	-	10	-	10	pF
C _O	output capacitance		-	4	-	-	-	-	-	pF
74AHCT245										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -8.0 mA	3.94	-	-	3.80	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	±0.25	-	±2.5	-	±10.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	4.0	-	40	-	80	μA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} - 2.1 V; other pins at V _{CC} or GND; I _O = 0 A; V _{CC} = 4.5 V to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C _I	input capacitance	V _I = V _{CC} or GND	-	3	10	-	10	-	10	pF
C _O	output capacitance		-	4	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74AHC245										
t _{pd}	propagation delay	An to Bn; Bn to An; see Figure 5	[2]							
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	5.0	8.4	1.0	10.0	1.0	10.5	ns
		C _L = 50 pF	-	6.5	11.9	1.0	13.5	1.0	15.0	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.5	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		5.0	7.5	1.0	8.5	1.0	9.5	ns
t _{en}	enable time	\overline{OE} to An; \overline{OE} to Bn; signal name DIR; see Figure 6	[3]							
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	6.5	13.2	1.0	15.5	1.0	16.5	ns
		C _L = 50 pF	-	9.0	16.7	1.0	19.0	1.0	21.0	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	4.0	8.5	1.0	10.0	1.0	11.0	ns
		C _L = 50 pF	-	5.0	10.6	1.0	12.0	1.0	13.5	ns
t _{dis}	disable time	\overline{OE} to An; \overline{OE} to Bn; signal name DIR; see Figure 6	[4]							
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	7.5	12.5	1.0	15.5	1.0	16.0	ns
		C _L = 50 pF	-	10.0	15.8	1.0	18.0	1.0	20.0	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	4.5	7.8	1.0	9.2	1.0	10.0	ns
		C _L = 50 pF	-	6.0	9.7	1.0	11.0	1.0	12.5	ns
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC}	[5]	-	12	-	-	-	-	pF

74AHCT245; V_{CC} = 4.5 V to 5.5 V

t _{pd}	propagation delay	An to Bn; Bn to An; see Figure 5	[2]							
		C _L = 15 pF	-	3.5	7.7	1.0	8.5	1.0	10.0	ns
		C _L = 50 pF	-	4.5	8.7	1.0	9.5	1.0	11.0	ns
t _{en}	enable time	\overline{OE} to An; \overline{OE} to Bn; signal name DIR; see Figure 6	[3]							
		C _L = 15 pF	-	5.0	13.8	1.0	15.0	1.0	17.5	ns
		C _L = 50 pF	-	6.0	14.8	1.0	16.0	1.0	18.5	ns

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
t _{dis}	disable time	OE to An; OE to Bn; signal name DIR; see Figure 6								
		C _L = 15 pF	-	5.0	14.4	1.0	15.5	1.0	18.0	ns
		C _L = 50 pF	-	6.0	15.4	1.0	16.5	1.0	19.5	ns
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC}								pF

[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] t_{en} is the same as t_{PZL} and t_{PZH}.

[4] t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

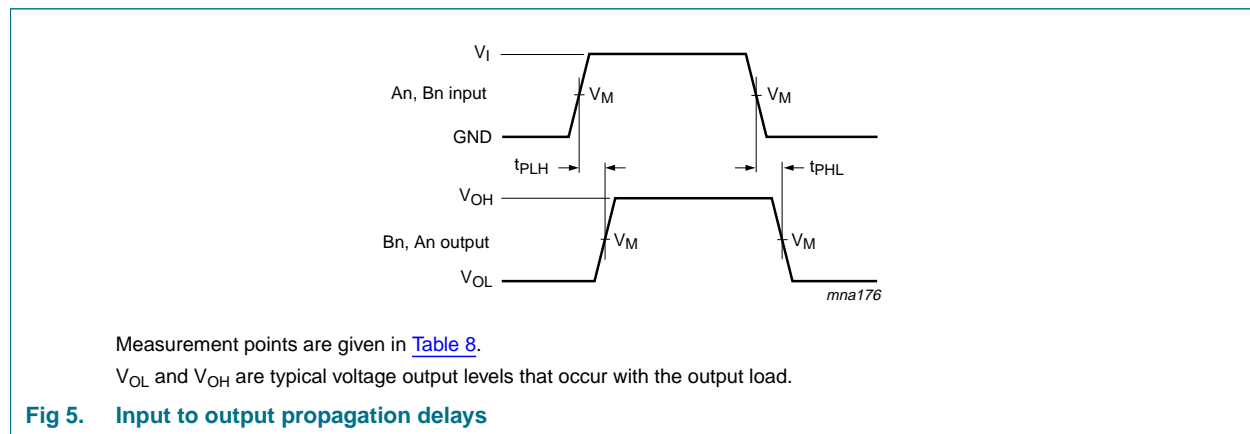
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

10.1 Waveforms



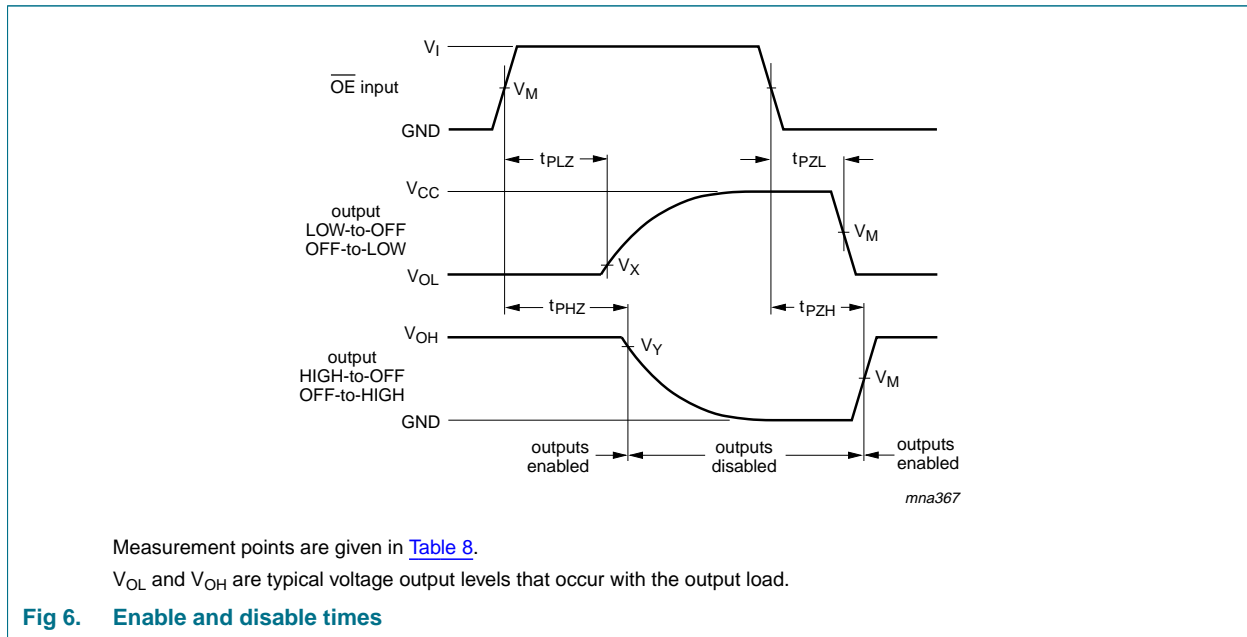


Table 8. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74AHC245	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$
74AHCT245	1.5 V	$0.5 \times V_{CC}$	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$

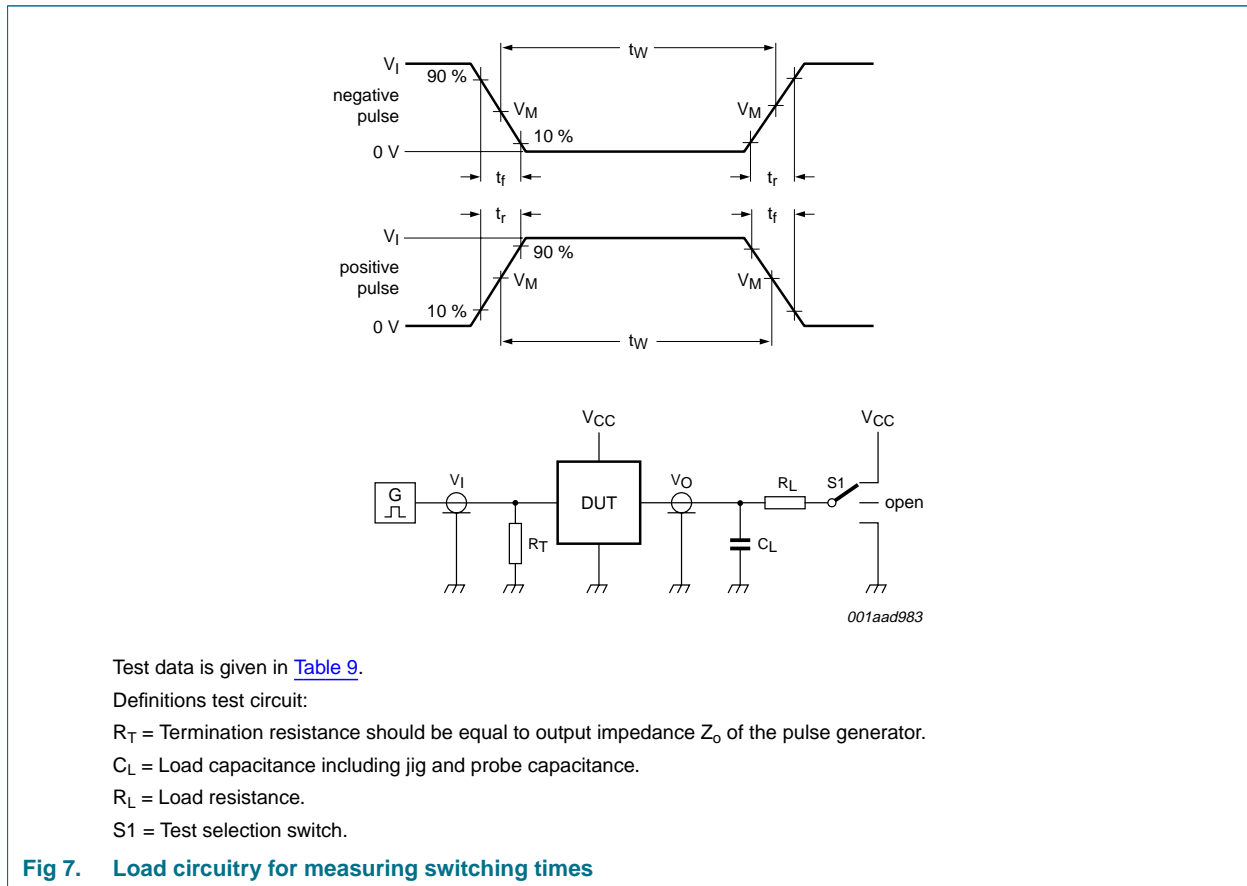


Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC245	V_{CC}	≤ 3.0 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74AHCT245	3.0 V	≤ 3.0 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

11. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

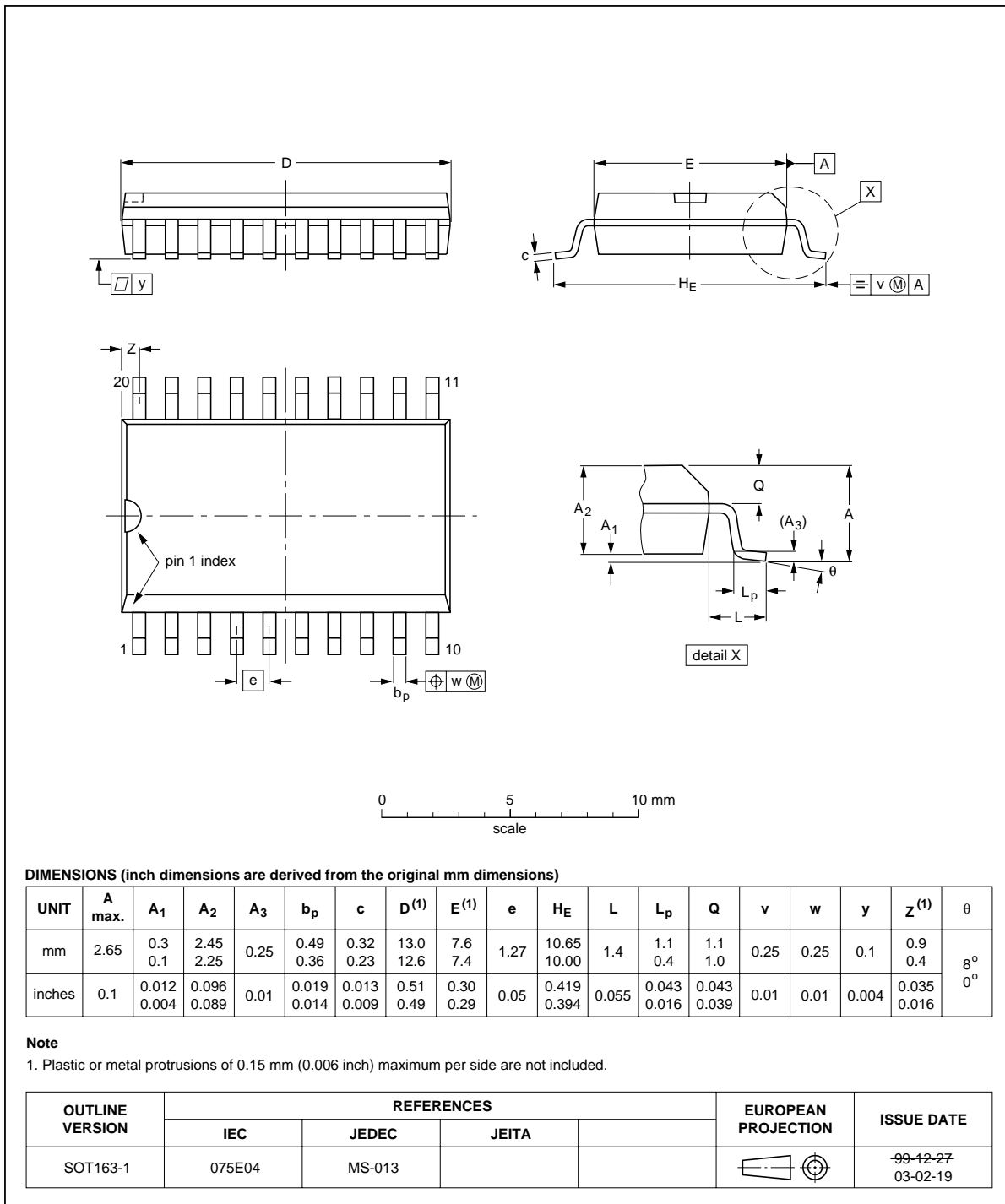


Fig 8. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

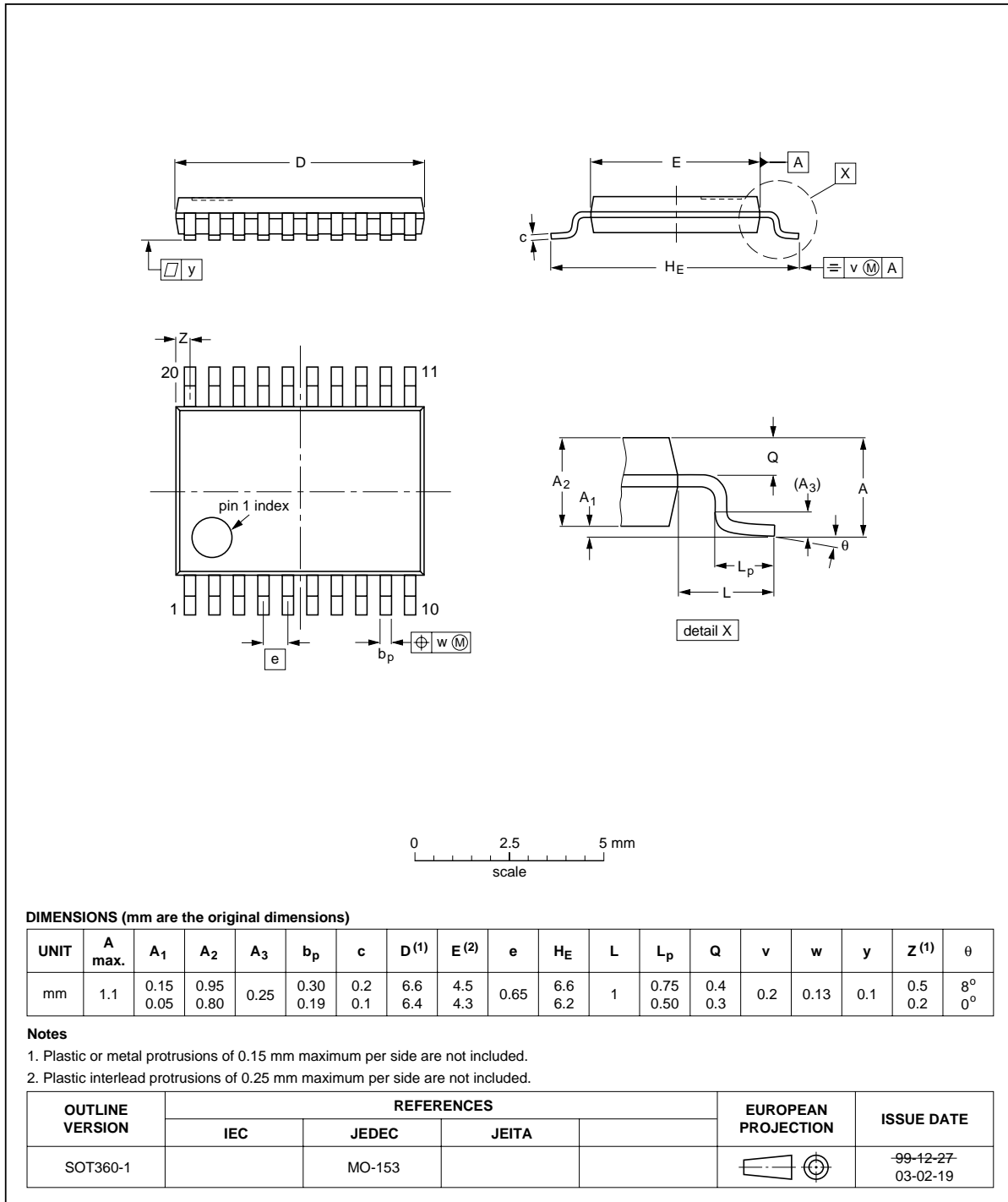


Fig 9. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm **SOT764-1**

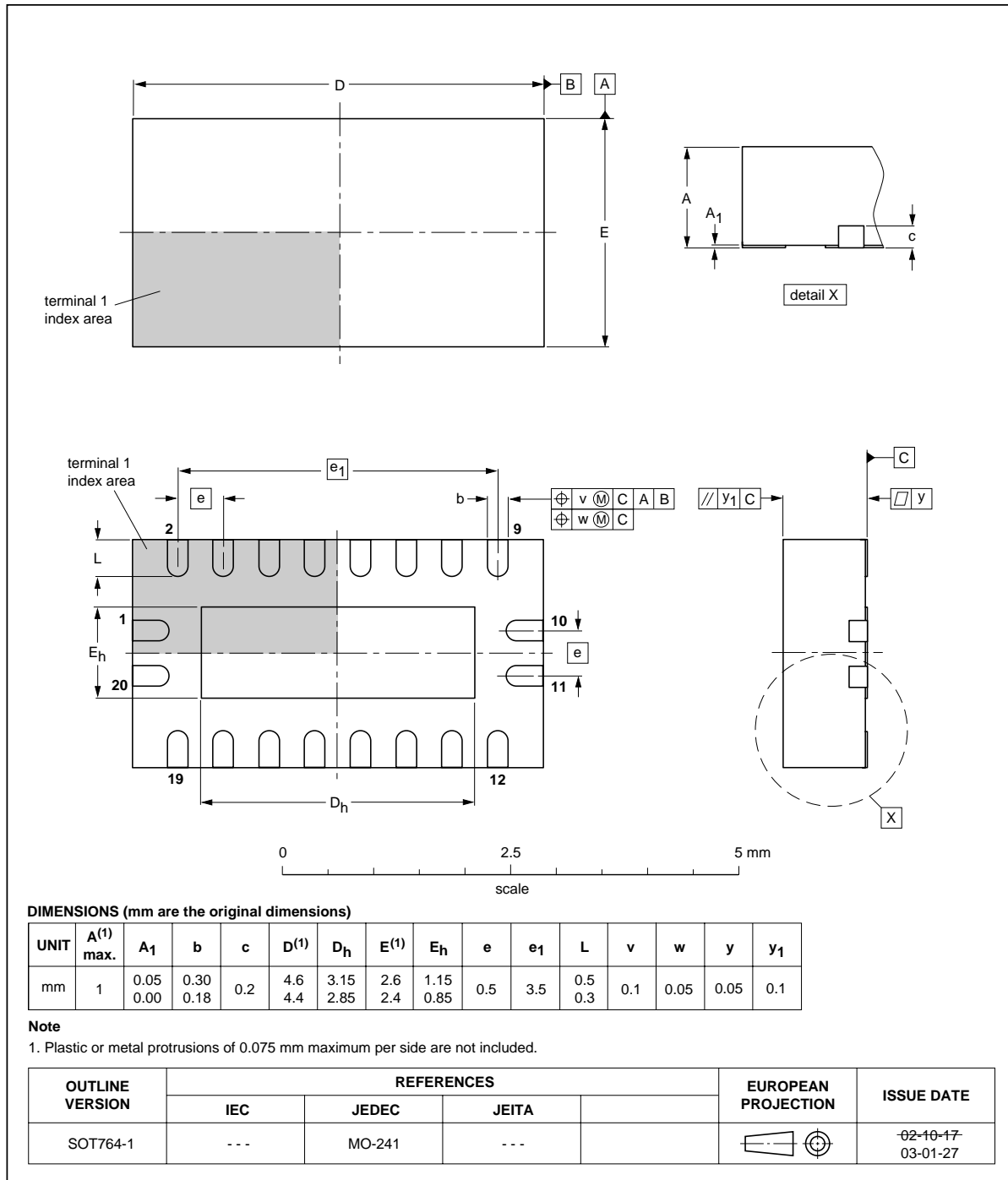


Fig 10. Package outline SOT764-1 (DHVQFN20)

12. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

13. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT245_5	20090428	Product data sheet	-	74AHC_AHCT245_4
Modifications:	<ul style="list-style-type: none"> • Section 3: DHVQFN20 package added. • Section 7: derating values added for DHVQFN20 package. • Section 11: outline drawing added for DHVQFN20 package. 			
74AHC_AHCT245_4	20080425	Product data sheet	-	74AHC_AHCT245_N_3
74AHC_AHCT245_N_3	20070925	Product data sheet	-	74AHC_AHCT245_2
74AHC_AHCT245_2	19990928	Product specification	-	74AHC_AHCT245_1
74AHC_AHCT245_1	19980921	Product specification	-	-

14. Legal information

14.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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